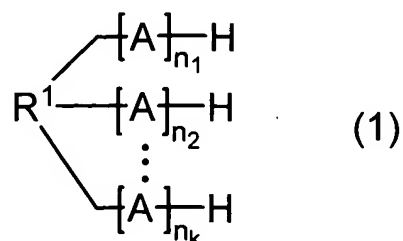
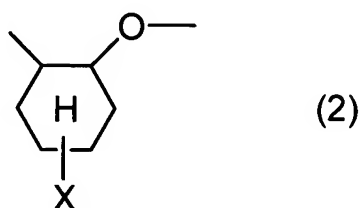


A. Amendments to the claims:

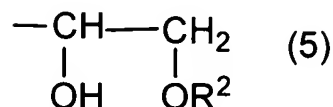
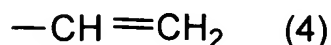
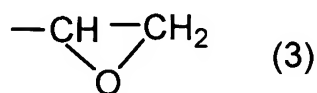
1. (Original) A method for producing a pattern formation mold, characterized in that the method comprises: a first step of applying to a substrate a radiation-sensitive negative-type resist composition containing an epoxy resin represented by formula (1):



(wherein R¹ represents a moiety derived from an organic compound having k active hydrogen atoms (k represents an integer of 1 to 100); each of n₁, n₂, through n_k represents 0 or an integer of 1 to 100; the sum of n₁, n₂, through n_k falls within a range of 1 to 100; and each of "A"s, which may be identical to or different from each other, represents an oxycyclohexane skeleton represented by formula (2):



(wherein X represents any of groups represented by formulas (3) to (5):



(wherein R² represents a hydrogen atom, an alkyl group, or an acyl group), and at least two groups represented by formula (3) are contained in one molecule of the epoxy resin)), along with a radiation-sensitive cationic polymerization initiator, and a solvent for dissolving the epoxy resin therein; a second step of drying the substrate coated with the radiation-sensitive negative-type resist composition, to thereby form a resist film; a third step of selectively exposing the formed resist film to an active energy beam according to a desired pattern; a fourth step of heating the exposed resist film so as to enhance a contrast of a pattern to be formed; a fifth step of developing the heated resist film, to thereby remove the unexposed area of the resist film through dissolution, thereby forming a patterned layer; and a sixth step of applying to the patterned layer a material other than that of the patterned layer such that spaces present in the patterned layer are filled, at least to some height, with the material, to thereby form a second layer, and removing the second layer, to thereby yield a pattern formation mold.

2. (Original) A method for producing a pattern formation mold according to claim 1, wherein the second layer is formed through metal plating.

3. (Original) A method for producing a pattern formation mold according to claim 1, wherein the second layer is formed by casting a photo-curable or heat-curable resin and curing the resin by light or heat.

4. (Currently Amended) A method for producing a pattern formation mold according to claim 1 ~~any one of claims 1 to 3~~, wherein the resist film formed by drying the radiation-sensitive negative-type resist composition has a softening point falling within a range of 30 to 120°C.

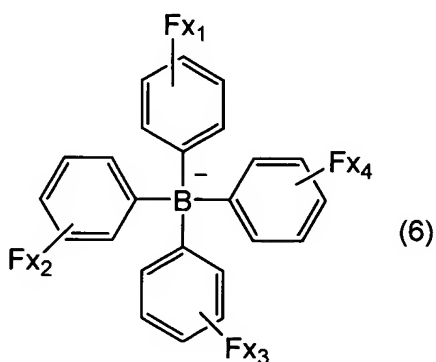
5. (Currently Amended) A method for producing a pattern formation mold according to claim 1 ~~any one of claims 1 to 4~~, wherein the epoxy resin has a softening point of 30°C or higher.

6. (Currently Amended) A method for producing a pattern formation mold according to claim 1 ~~any one of claims 1 to 5~~, wherein the radiation-sensitive cationic polymerization initiator comprises one or more sulfonium salts.

7. (Currently Amended) A method for producing a pattern formation mold according to claim 1 ~~any one of claims 1 to 6~~, wherein the radiation-sensitive cationic polymerization initiator has one or more anion moieties, at least one species of the anion moieties being

SbF_6^- .

8. (Currently Amended) A method for producing a pattern formation mold according to claim 1 ~~any one of claims 1 to 7~~, wherein the radiation-sensitive cationic polymerization initiator has one or more anion moieties, at least one species of the anion moieties being a borate represented by formula (6):



(wherein each of x_1 to x_4 represents an integer of 0 to 5, and the sum $x_1 + x_2 + x_3 + x_4$ is 1 or more).

9. (Currently Amended) A method for producing a pattern formation mold according to claim 1 ~~any one of claims 1 to 8~~, wherein the active energy beam is an X-ray having a wavelength of 0.1 to 5 nm.

10. (Currently Amended) A method for producing a pattern formation mold according to claim 1 ~~any one of claims 1 to 9~~, wherein the resist film has a thickness of at least 50 μm .